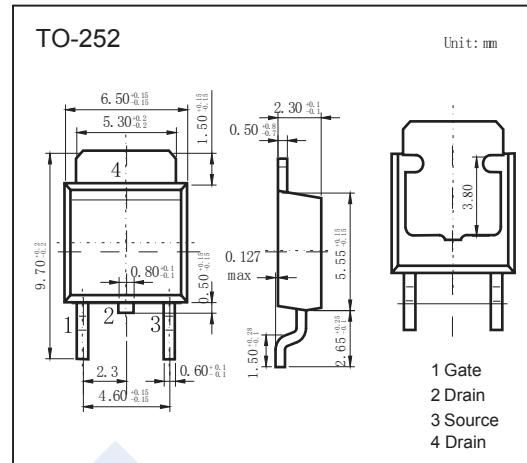
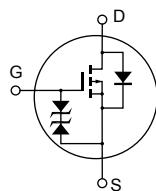


P-Channel MOSFET

2SJ319S

■ Features

- V_{DS} (V) = -200V
- I_D = -3 A (V_{GS} = -10V)
- $R_{DS(ON)}$ < 2.3 Ω (V_{GS} = -10V)
- High speed switching
- Low drive current



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-200	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	-3	A
Pulsed Drain Current (Note.1)	I_{DM}	-12	
Body to Drain Diode Reverse Drain Current	I_{DR}	-3	
Power Dissipation $T_c = 25^\circ\text{C}$	P_D	20	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $P_W \leq 10 \text{ ms}$, duty cycle $\leq 1\%$

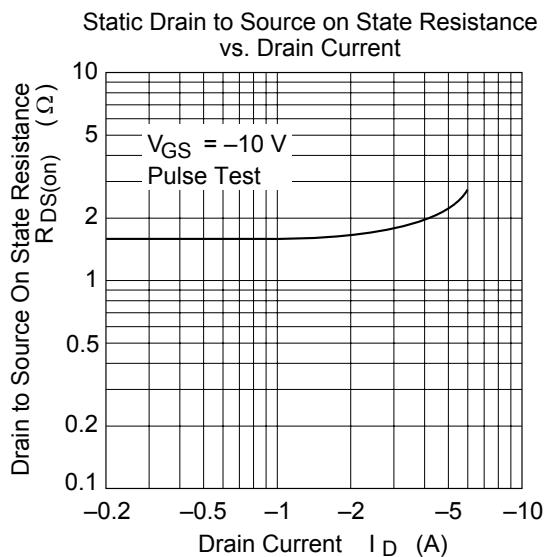
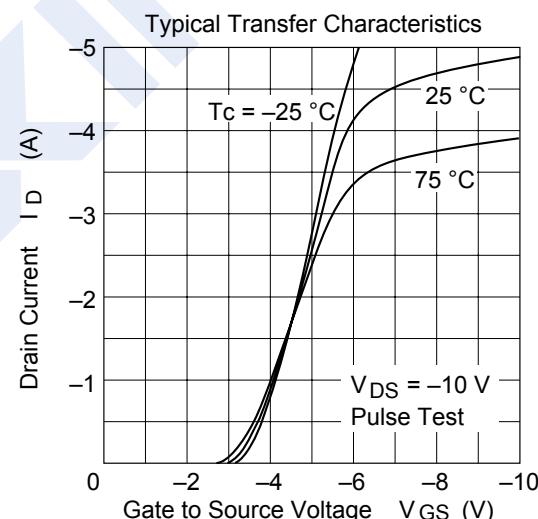
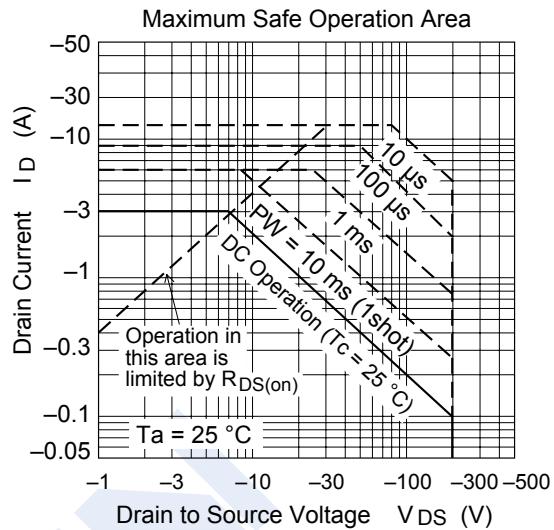
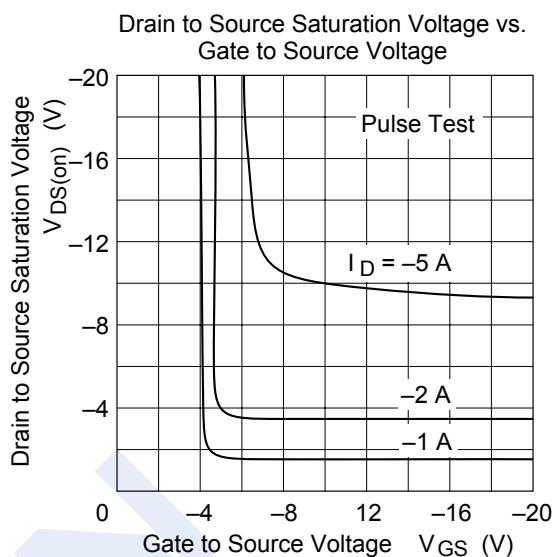
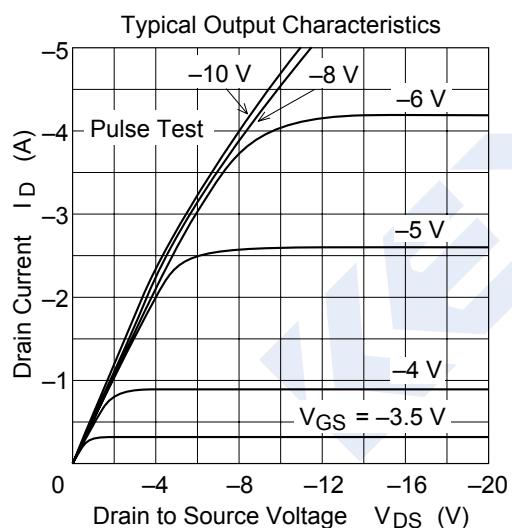
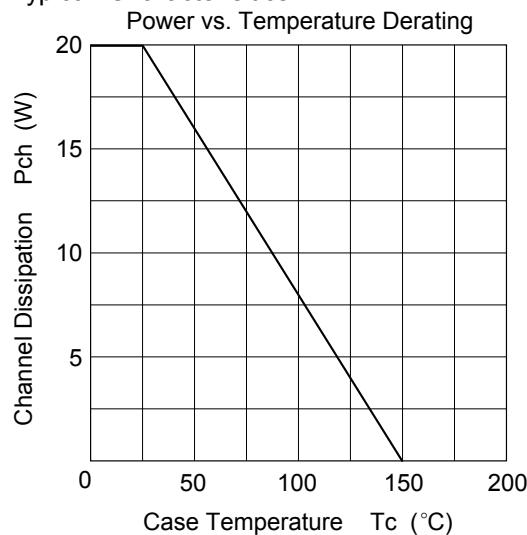
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -10\text{mA}$, $V_{GS} = 0\text{V}$	-200			V
Gate to Source Breakdown Voltage	V_{GSS}	$I_G = \pm 100 \mu\text{A}$, $V_{DS} = 0\text{V}$	± 20			
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -160\text{V}$, $V_{GS} = 0\text{V}$			-100	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 16\text{V}$			± 10	μA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -10\text{V}$ $I_D = -1\text{mA}$	-2		-4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{V}$, $I_D = -2\text{A}$			2.3	Ω
Forward Transconductance	g_{FS}	$V_{DS} = -10\text{V}$, $I_D = -2\text{A}$	1	1.7		S
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -10\text{V}$, $f = 1\text{MHz}$		330		pF
Output Capacitance	C_{oss}			130		
Reverse Transfer Capacitance	C_{rss}			25		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -10\text{V}$, $I_D = -2\text{A}$, $R_L = 15\Omega$		10		ns
Turn-On Rise Time	t_r			30		
Turn-Off Delay Time	$t_{d(off)}$			40		
Turn-Off Fall Time	t_f			30		
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -3\text{A}$, $V_{GS} = 0$, $di/dt = 50\text{A}/\mu\text{s}$	180			
Diode Forward Voltage	V_{SD}	$I_S = -3\text{A}$, $V_{GS} = 0\text{V}$		-1.15		V

P-Channel MOSFET

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■ Typical Characteristics

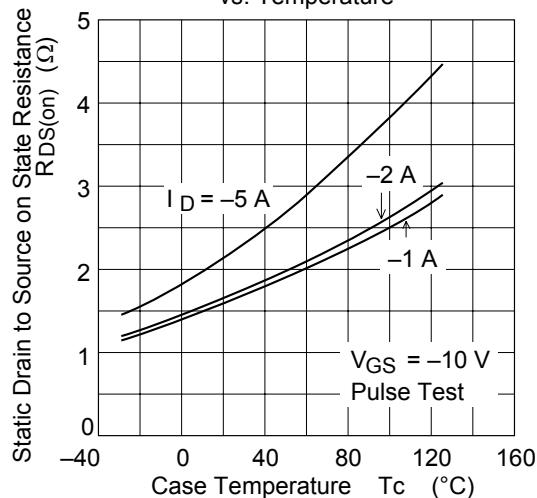


P-Channel MOSFET

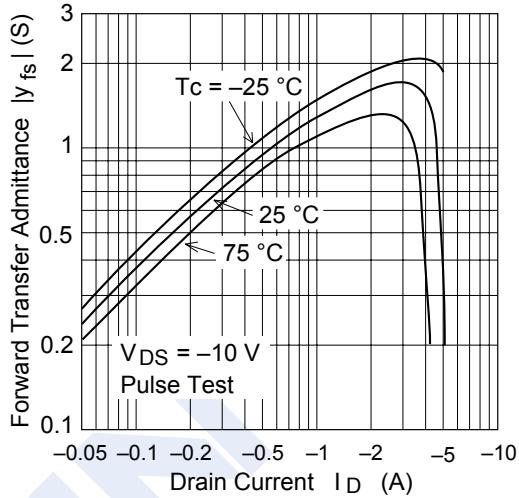
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■ Typical Characteristics

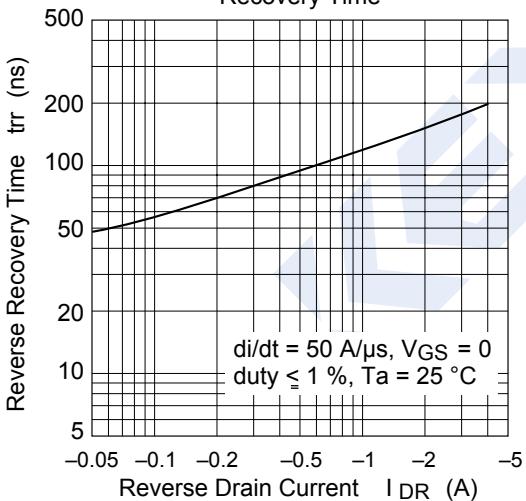
Static Drain to Source on State Resistance vs. Temperature



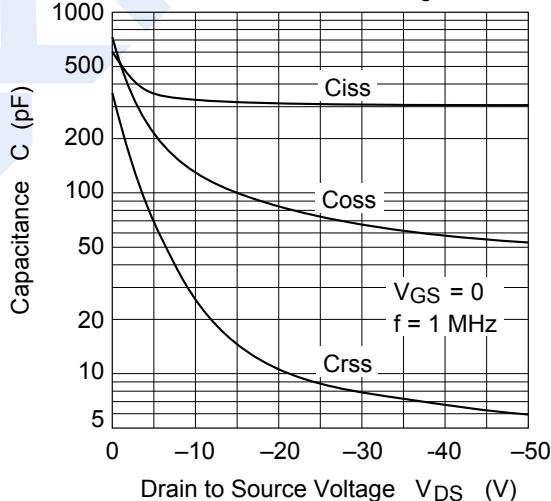
Forward Transfer Admittance vs. Drain Current



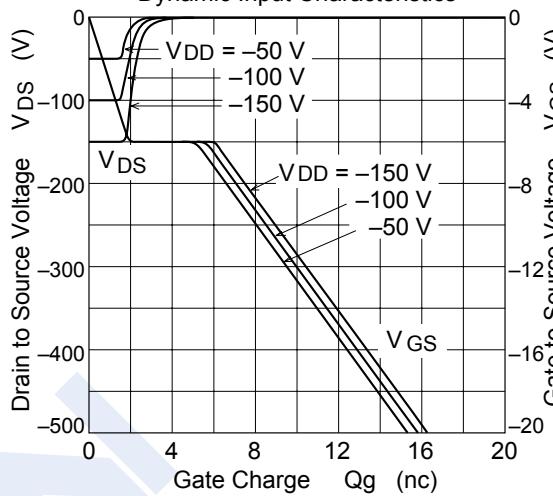
Body-Drain Diode Reverse Recovery Time



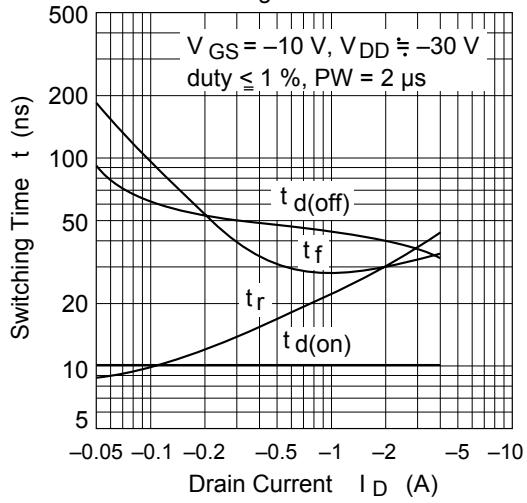
Typical Capacitance vs. Drain to Source Voltage



Dynamic Input Characteristics



Switching Characteristics



P-Channel MOSFET

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■ Typical Characteristics

